



March 2015



FDD3706/FDU3706

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20V N-Channel PowerTrench[®] MOSFET

General Description

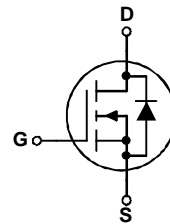
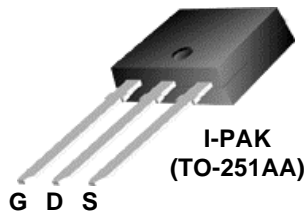
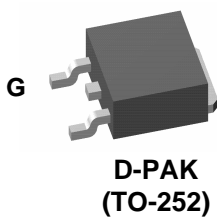
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$, fast switching speed and extremely low $R_{DS(ON)}$ in a small package.

Applications

- DC/DC converter
- Motor Drives

Features

- 50 A, 20 V $R_{DS(ON)} = 9\text{ m}\Omega @ V_{GS} = 10\text{ V}$
 $R_{DS(ON)} = 11\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
 $R_{DS(ON)} = 16\text{ m}\Omega @ V_{GS} = 2.5\text{ V}$
- Low gate charge (16 nC)
- Fast Switching
- High performance trench technology for extremely low $R_{DS(ON)}$



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	± 12	V
I _D	Continuous Drain Current @ T _C =25°C (Note 3)	50	A
	@ T _A =25°C (Note 1a)	14.7	
	Pulsed (Note 1a)	60	
P _D	Power Dissipation @ T _C =25°C (Note 3)	44	W
	@ T _A =25°C (Note 1a)	3.8	
	@ T _A =25°C (Note 1b)	1.6	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +175	°C

Thermal Characteristics

R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	3.4	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	45	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1b)	96	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape width	Quantity
FDD3706	FDD3706	D-PAK (TO-252)	13"	16mm	2500 units
FDU3706	FDU3706	I-PAK (TO-251)	Tube	N/A	75

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Drain-Source Avalanche Ratings (Note 2)

E_{AS}	Drain-Source Avalanche Energy	Single Pulse, $V_{DD} = 10\text{V}$, $I_D = 7\text{A}$			60	mJ
I_{AS}	Drain-Source Avalanche Current				7	A

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}$, $I_D = 250\ \mu\text{A}$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		13		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{V}$, $V_{GS} = 0\text{V}$			1	μA
I_{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 12\text{V}$, $V_{DS} = 0\text{V}$			100	nA
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -12\text{V}$, $V_{DS} = 0\text{V}$			-100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	0.5	1	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		-3.5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{V}$, $I_D = 16.2\text{A}$ $V_{GS} = 4.5\text{V}$, $I_D = 14.7\text{A}$ $V_{GS} = 2.5\text{V}$, $I_D = 12.2\text{A}$ $V_{GS} = 4.5\text{V}$, $I_D = 14.7\text{A}$, $T_J = 125^\circ\text{C}$		7.5 8 11 12.6	9 11 16 19	m Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 4.5\text{V}$, $V_{DS} = 5\text{V}$	30			A
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{V}$, $I_D = 14.7\text{A}$		65		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 10\text{V}$, $V_{GS} = 0\text{V}$, $f = 1.0\text{MHz}$		1882		pF
C_{oss}	Output Capacitance			430		pF
C_{rss}	Reverse Transfer Capacitance			201		pF

Switching Characteristics (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10\text{V}$, $I_D = 1\text{A}$, $V_{GS} = 4.5\text{V}$, $R_{GEN} = 6\ \Omega$		11	20	ns
t_r	Turn-On Rise Time			15	27	ns
$t_{d(off)}$	Turn-Off Delay Time			35	56	ns
t_f	Turn-Off Fall Time			16	29	ns
Q_g	Total Gate Charge	$V_{DS} = 10\text{V}$, $I_D = 14.7\text{A}$, $V_{GS} = 4.5\text{V}$		16	23	nC
Q_{gs}	Gate-Source Charge			3.7		nC
Q_{gd}	Gate-Drain Charge			4		nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current			3.2		A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = 3.2\text{A}$ (Note 2)		0.7	1.2	V

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $R_{\theta JA} = 40^\circ\text{C/W}$ when mounted on a 1in^2 pad of 2 oz copper



b) $R_{\theta JA} = 96^\circ\text{C/W}$ when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

3. Maximum current is calculated as:

$$I_{D(max)} = \sqrt{\frac{P_D}{R_{DS(on)}}}$$

where P_D is maximum power dissipation at $T_C = 25^\circ\text{C}$ and $R_{DS(on)}$ is at $T_{J(max)}$ and $V_{GS} = 10\text{V}$. Package current limitation is 21A

Typical Characteristics

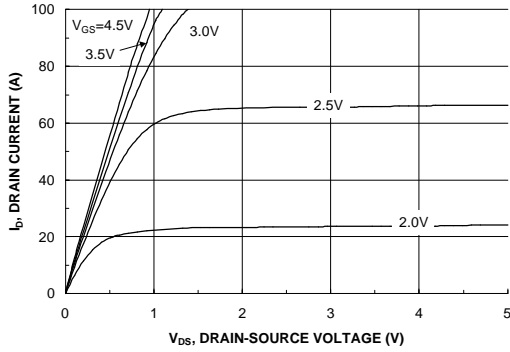


Figure 1. On-Region Characteristics

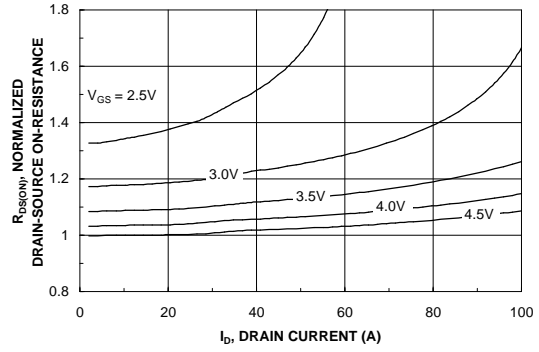


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

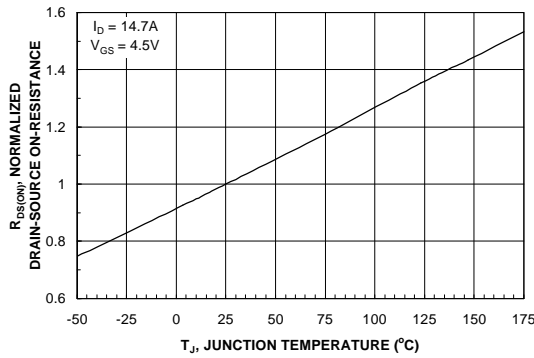


Figure 3. On-Resistance Variation with Temperature

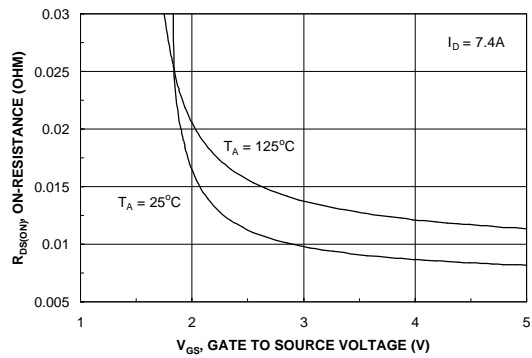


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

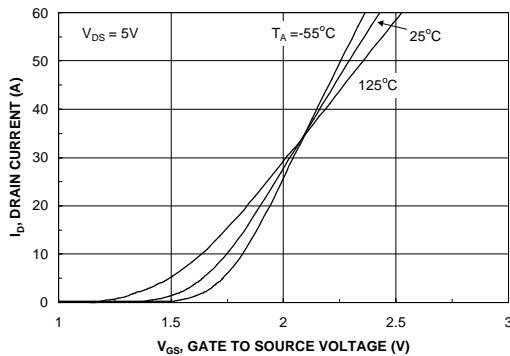


Figure 5. Transfer Characteristics

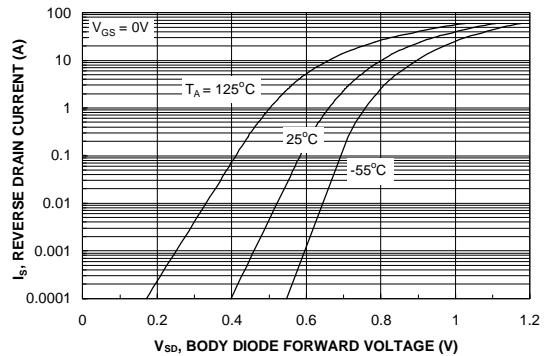


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Characteristics

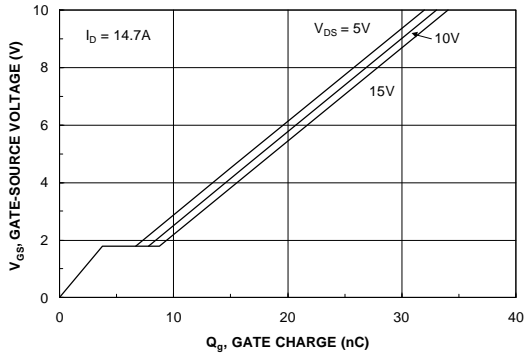


Figure 7. Gate Charge Characteristics

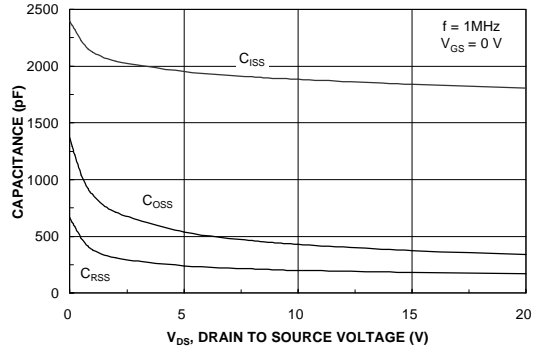


Figure 8. Capacitance Characteristics

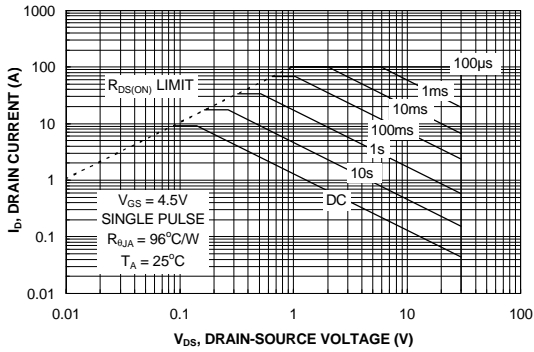


Figure 9. Maximum Safe Operating Area

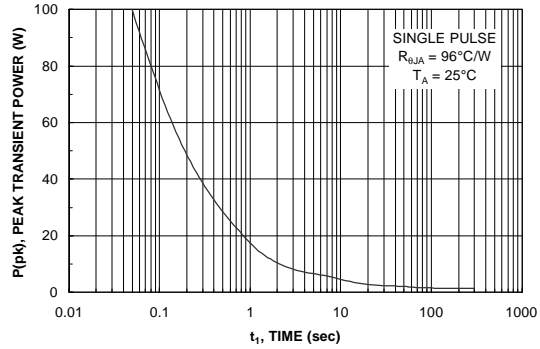


Figure 10. Single Pulse Maximum Power Dissipation

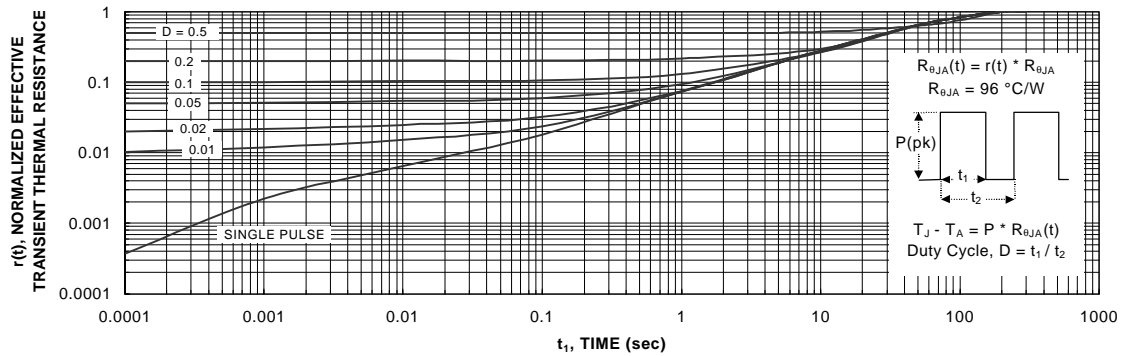
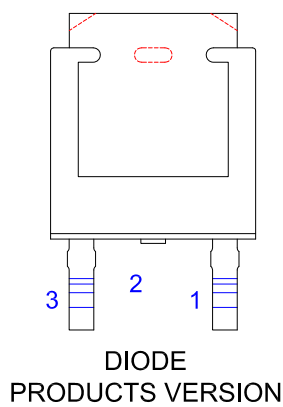
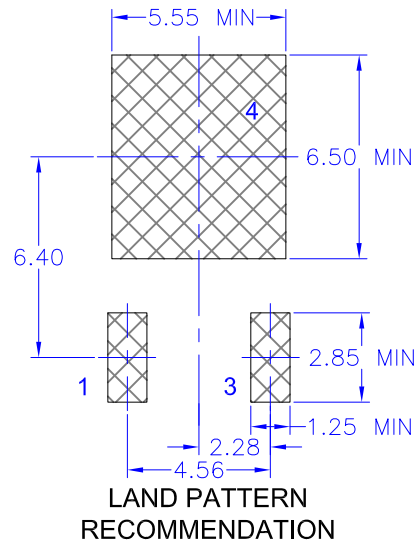


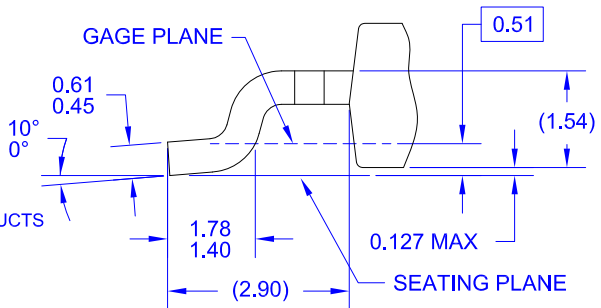
Figure 11. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.



NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
- E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS
- F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
- H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



DETAIL A
(ROTATED -90°)
SCALE: 12X



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